

App. No. 10/501,791  
Reply dated August 29, 2005 to  
"Notice of Non-Compliant Amendment"

**Amendments to the Specification (other than claims):**

Please replace the current title with the following amended title:

**CERAMICS HEATER CERAMIC SUSCEPTOR FOR SEMICONDUCTOR  
PRODUCTION SYSTEM MANUFACTURING EQUIPMENT**

Please replace the paragraph beginning at page 9, line 2, with the following rewritten paragraph:

A paste of  $Y_2O_3$  adhesive agent kneaded with a binder was print-coated on the surface of the remaining AlN substrate, which was then degreased at 500°C. The adhesive layer of this AlN substrate was then overlaid on the side of the AlN substrate on which the resistive heating element was formed, and the substrates were bonded by heating at 800°C. Sample ceramic susceptors having the Fig. [[1]] 2 configuration and differing in inter-line separation  $L$  and sectional smallest angle  $\theta$  as set forth in the following Table I were thus produced.

Please replace the paragraph beginning at page 11, line 17, with the following rewritten paragraph:

A paste of  $SiO_2$  adhesive agent kneaded with binder was print-coated on the surface of the other  $Si_3N_4$  substrate, which was then degreased at 500°C. The adhesive layer of this  $Si_3N_4$  substrate was then overlaid on the side of the  $Si_3N_4$  substrate on which the resistive heating element was formed, and the substrates were bonded by heating at 800°C. Sample ceramic susceptors having the Fig. [[1]] 2 configuration and differing in inter-line separation  $L$  and sectional smallest angle  $\theta$  as set forth in the following Table II were thus produced.

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Please replace the paragraph beginning at page 14, line 3, with the following rewritten paragraph:

A paste of  $\text{SiO}_2$  adhesive agent kneaded with a binder was print-coated on the surface of the other AION substrate, which was then degreased at  $500^\circ\text{C}$ . The adhesive layer of this AION substrate was then overlaid on the side of the AION substrate on which the resistive heating element was formed, and the substrates were bonded by heating at  $800^\circ\text{C}$ . Sample ceramic susceptors having the Fig. [[1]] 2 configuration and differing in inter-line separation  $L$  and sectional smallest angle  $\theta$  as set forth in the following Table III were thus produced.

Please replace the paragraph beginning at page 19, line 3, with the following rewritten paragraph:

The resulting laminates were degreased for 5 hours at  $600^\circ\text{C}$  in a non-oxidizing atmosphere, then hot-pressed at  $1800^\circ\text{C}$  while applying pressure of 100 to  $150 \text{ kg/cm}^2$ , thereby producing 3 mm thick AlN plates. These plates were then cut to form 380-mm diameter disks, and the periphery of each disk was polished to a 300 mm diameter. Sample ceramic susceptors having the Fig. [[2]] 3 configuration internal featuring a tungsten resistive heating element and plasma electrode and differing in inter-line separation  $L$  and sectional smallest angle  $\theta$  as set forth in the following Table V were thus produced.